TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC74VHC245F,TC74VHC245FT,TC74VHC245FK

#### Octal Bus Transceiver

The TC74VHC245 is an advanced high speed CMOS OCTAL BUS TRANSCEIVER fabricated with silicon gate C<sup>2</sup>MOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

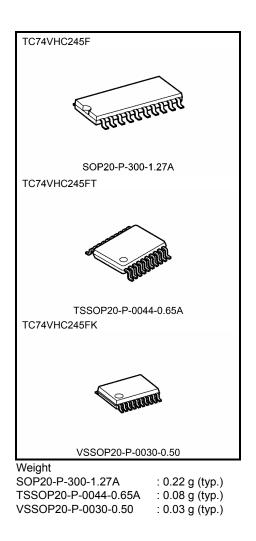
It is intended for two-way asynchronous communication between data busses. The direction of data transmission is determined by the level of the DIR input.

The enable input  $(\overline{G})$  can be used to disable the device so that the busses are effectively isolated.

All inputs are equipped with protection circuits against static discharge.

## Features (Note 1) (Note 2) (Note 3)

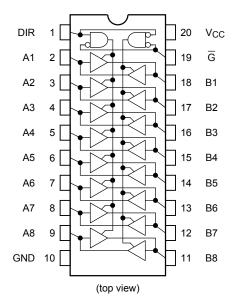
- High speed:  $t_{pd} = 4.0$  ns (typ.) at VCC = 5 V
- Low power dissipation:  $I_{CC} = 4 \ \mu A \ (max)$  at  $Ta = 25^{\circ}C$
- High noise immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (min)
- Balanced propagation delays:  $t_{pLH} \simeq t_{pHL}$
- Wide operating voltage range:  $V_{CC}$  (opr) = 2 V to 5.5 V
- Low noise: VOLP = 1.2 V (max)
- Pin and function compatible with 74ALS245
  - Note 1: Do not apply a signal to any bus terminal when it is in the output mode. Damage may result.
  - Note 2: All floating (high impedance) bus terminals must have their input levels fixed by means of pull up or pull down resistors.
  - Note 3: A parasitic diode is formed between the bus and V<sub>CC</sub> terminals. Therefore bus terminal can not be used to interface 5 V to 3 V systems directly.



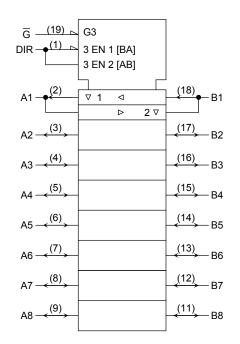
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# <u>TOSHIBA</u>

## **Pin Assignment**



#### **IEC Logic Symbol**



#### Truth Table

Inputs		Fund	Output			
G	DIR	A Bus	B Bus	Output		
L	L	Output	Input	A = B		
L	Н	Input Output		Input Output		B = A
Н	Х	Ž	Z			

X: Don't care

Z: High impedance

## **Absolute Maximum Ratings (Note)**

Characteristics	Symbol	Rating	Unit
Supply voltage range	Vcc	-0.5 to 7.0	V
DC input voltage (DIR, $\overline{G}$ )	V <sub>IN</sub>	-0.5 to 7.0	V
DC bus I/O voltage	V <sub>I/O</sub>	-0.5 to V <sub>CC</sub> + 0.5	V
Input diode current	IIK	-20	mA
Output diode current	IOK	±20	mA
DC output current	lout	±25	mA
DC V <sub>CC</sub> /ground current	ICC	±75	mA
Power dissipation	PD	180	mW
Storage temperature	T <sub>stg</sub>	-65 to 150	°C

Note: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

## **Operating Ranges (Note)**

Characteristics	Symbol	Rating	Unit	
Supply voltage	V <sub>CC</sub>	2.0 to 5.5	V	
Input voltage (DIR, G)	V <sub>IN</sub>	0 to 5.5	V	
Bus I/O voltage	V <sub>I/O</sub>	0 to V <sub>CC</sub>	V	
Operating temperature	T <sub>opr</sub>	-40 to 85	°C	
Input rise and fall time	dt/dv	0 to 100 (V <sub>CC</sub> = 3.3 ± 0.3 V)	ns/V	
	ul/uv	0 to 20 (V <sub>CC</sub> = 5 $\pm$ 0.5 V)		

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs and bus inputs must be tied to either VCC or GND. Please connect both bus inputs and the bus outputs with VCC or GND when the I/O of the bus terminal changes by the function. In this case, please note that the output is not short-circuited.

## **Electrical Characteristics**

#### **DC Characteristics**

Characteristics	Symbol	Test Condition		Ta = 25°C			Ta = -40 to 85°C		Unit	
Characteristics	Gymbol				Min	Тур.	Max	Min	Max	Onit
High-level input voltage	VIH	_		2.0 3.0 to 5.5	1.50 V <sub>CC</sub> × 0.7		_	1.50 V <sub>CC</sub> × 0.7		V
Low-level input voltage	VIL	_		2.0 3.0 to 5.5	_		0.50 V <sub>CC</sub> × 0.3		0.50 V <sub>CC</sub> × 0.3	V
High-level output voltage	V <sub>OH</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = -50 μA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5	_ _ _	1.9 2.9 4.4		v
			I <sub>OH</sub> = -4 mA I <sub>OH</sub> = -8 mA	3.0 4.5	2.58 3.94		_	2.48 3.80		
Low-level output voltage	V <sub>OL</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 50 μA	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1	_ _ _	0.1 0.1 0.1	V
			I <sub>OL</sub> = 4 mA I <sub>OL</sub> = 8 mA	3.0 4.5	_		0.36 0.36	_ _	0.44 0.44	
3-state output off-state current	I <sub>OZ</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$		5.5		_	±0.25	_	±2.50	μA
Input leakage current	lıN	V <sub>IN</sub> = 5.5 V or GND		0 to 5.5	_	—	±0.1	—	±1.0	μA
Quiescent supply current	ICC	V <sub>IN</sub> = V <sub>CC</sub> or GND		5.5	_	_	4.0	_	40.0	μA

#### AC Characteristics (input: tr = tf = 3 ns)

Characteristics	Symbol	Test Condition		Ta = 25°C			Ta = −40 to 85°C		Unit	
	- <b>,</b>		V <sub>CC</sub> (V)	C <sub>L</sub> (pF)	Min	Тур.	Max	Min	Max	
			3.3 ± 0.3	15	_	5.8	8.4	1.0	10.0	
Propagation delay	t <sub>pLH</sub>		$5.5 \pm 0.5$	50	-	8.3	11.9	1.0	13.5	ns
time	t <sub>pHL</sub>	_	5.0 ± 0.5	15	-	4.0	5.5	1.0	6.5	
			$5.0 \pm 0.5$	50	-	5.5	7.5	1.0	8.5	
			3.3 ± 0.3	15		8.5	13.2	1.0	15.5	
3-state output enable	t <sub>pZL</sub> t <sub>pZH</sub>	R <sub>L</sub> = 1 kΩ	$3.3 \pm 0.3$	50	-	11.0	16.7	1.0	19.0	ns
time			5.0 ± 0.5	15		5.8	8.5	1.0	10.0	
				50	-	7.3	10.6	1.0	12.0	
3-state output disable	t <sub>pLZ</sub>	R <sub>L</sub> = 1 kΩ	3.3 ± 0.3	50	-	11.5	15.8	1.0	18.0	20
time	t <sub>pHZ</sub>		5.0 ± 0.5	50	-	7.0	9.7	1.0	11.0	ns
	t <sub>osLH</sub>		3.3 ± 0.3	50	-	_	1.5	_	1.5	
Output to output skew	t <sub>osHL</sub>	(Note 1)	5.0 ± 0.5	50	_	_	1.0	_	1.0	ns
Input capacitance	C <sub>IN</sub>	DIR, G	-		_	4	10		10	pF
Bus input capacitance	C <sub>I/O</sub>	A <sub>n</sub> , Bn			_	8			_	pF
Power dissipation capacitance	C <sub>PD</sub>			(Note 2)		21		_	_	pF

Note 1: Parameter guaranteed by design.

 $t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|$ 

Note 2: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8$  (per bit)

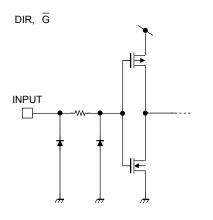
## Noise Characteristics (input: t<sub>r</sub> = t<sub>f</sub> = 3 ns) (Note)

Characteristics	Symbol	Test Condition		Ta = 25°C		Unit
Characteristics	Symbol		$V_{CC}(V)$	Тур.	Max	Onic
Quiet output maximum dynamic	Vola		5.0	0.7	1.0	V
V <sub>OL</sub>	Volp	C <sub>L</sub> = 50 pF	5.0	(0.9)	(1.2)	v
Quiet output minimum dynamic	Van	C <sub>I</sub> = 50 pF	5.0	-0.7	-1.0	V
V <sub>OL</sub>	V <sub>OLV</sub>	CL - 50 pr	5.0	(-0.9)	(-1.2)	
Minimum high level dynamic input voltage	VIHD	C <sub>L</sub> = 50 pF	5.0	_	3.5	V
Maximum low level dynamic input voltage	V <sub>ILD</sub>	C <sub>L</sub> = 50 pF	5.0	_	1.5	V

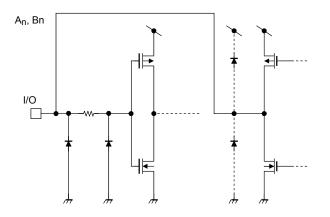
Note: The value in ( ) only applies to JEDEC SOP (FW) devices.

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## Input Equivalent Circuit



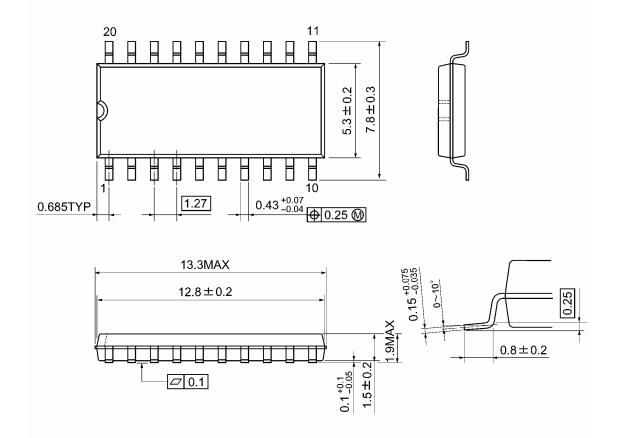
## **Bus Terminal Equivalent Circuit**



## **Package Dimensions**

SOP20-P-300-1.27A

Unit: mm



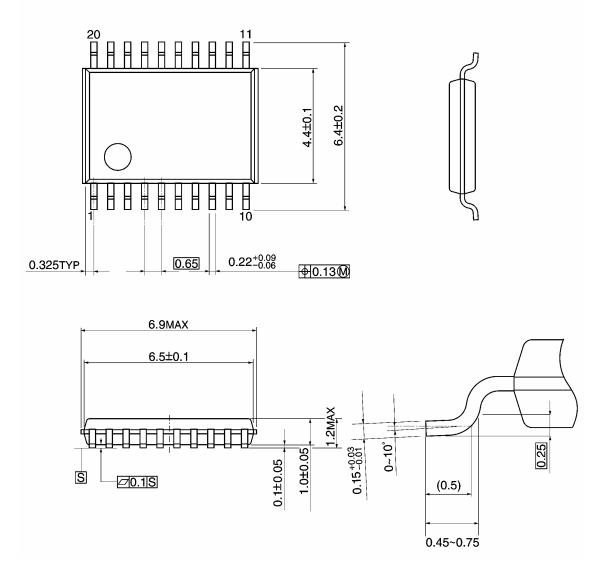
Weight: 0.22 g (typ.)

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## **Package Dimensions**

TSSOP20-P-0044-0.65A

Unit: mm



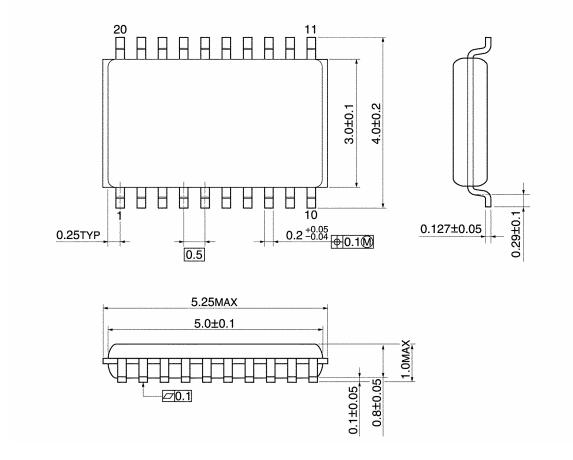
Weight: 0.08 g (typ.)

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## **Package Dimensions**

VSSOP20-P-0030-0.50

Unit: mm



Weight: 0.03 g (typ.)

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#### **RESTRICTIONS ON PRODUCT USE**

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